| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|---|---|---|---|---|---|---|
| S1 | 0 | (((first) near2 transistor) same (second near2 transistor) same ((floating adj gate) near2 transistor) same ((first or second or third) near heavily near (dope or doped)) same conductivity).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 12:37 |
| S2 | 0 | (((first) near2 transistor) same (second near2 transistor) same ((floating adj gate) near2 transistor) same ((first or second or third) near heavily near (dope or doped)) same conductivity) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 12:37 |
| S3 | 468 | (((first) near2 transistor) same (second near2 transistor) same ((floating adj gate) near2 transistor)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 12:37 |
| S4 | 204 | (((first) near2 transistor) same (second near2 transistor) same ((floating adj gate) near2 transistor)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 12:37 |
| S5 | 1 | (((first) near2 transistor) same (second near2 transistor) same ((floating adj gate) near2 transistor) same (esd or electrostatic)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 12:38 |
| S6 | 4 | ((((first) near2 transistor) same (second near2 transistor) same ((floating adj gate) near2 transistor)) and (esd or electrostatic)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 12:39 |
| S7 | 6 | ((((first) near2 transistor) same (second near2 transistor) same ((floating adj gate))) and (esd or electrostatic)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 12:41 |
| S8 | 376 | (((first) near2 transistor) same (second near2 transistor) same ((floating adj gate))).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 12:41 |
| S9 | 295 | ((((first) near2 transistor) with (second near2 transistor) with ((floating adj gate))).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 12:41 |

| S10 | 312 | (((first) near2 (mos of mosfet or transistor)) with (second near2 (mos or mosfet or transistor)) with ((floating adj gate))).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 12:42 |
|---|---|---|---|---|---|---|
| S11 | 6 | (((first) near2 (mos of mosfet or transistor)) with (second near2 (mos or mosfet or transistor)) with ((floating adj gate))).clm. and (esd or electrostatic).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 12:44 |
| S12 | 6 | (((first) near3 (mos of mosfet or transistor)) with (second near3 (mos or mosfet or transistor)) with ((floating adj gate) near3 transistor)).clm. and (esd or electrostatic).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 12:47 |
| S13 | 17121 | "257" and (esd or electrostatic) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 12:47 |
| S14 | 409 | "257" and (esd or electrostatic) and (floating adj gate) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 12:53 |
| S15 | 197 | "257" and (esd or electrostatic) and (floating adj gate).ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 12:48 |
| S16 | 62 | "257" and (esd or electrostatic).ti, ab,clm. and (floating adj gate).ti, ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 12:51 |
| S17 | 32 | "257" and (esd or electrostatic).ti, ab,clm. and (floating adj gate).ti, ab,clm. and (dope or doped or doping or conductivity or impurity).ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 12:49 |
| S18 | 46 | S14 and chen | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 12:53 |

| S19 | 64 | (US-20040041215-$ or US-20040004231-$ or US-20020195648-$ or US-20020005544-$ or US-20010039091-$ or US-20020140023-$ or US-20020014656-$).did. or (US-6809386-$ or US-5589699-$ or US-5519240-$ or US-4495427-$ or US-6826128-$ or US-6008508-$ or US-6670679-$ or US-6610262-$ or US-6560080-$ or US-6448593-$ or US-6388922-$ or US-6373095-$ or US-6265251-$ or US-6239465-$ or US-6055143-$ or US-5986308-$ or US-5932916-$ or US-5909347-$ or US-5869873-$ or US-5844300-$ or US-5838033-$ or US-5272586-$ or US-5195010-$ or US-4087795-$ or US-3590343-$ or US-6825525-$).did. or (US-6680505-$ or US-6597048-$ or US-6556025-$ or US-6426529-$ or US-6175394-$ or US-6133601-$ or US-5986939-$ or US-5506159-$ or US-6034552-$).did. or (JP-05343696-$ or JP-04324980-$ or JP-61230376-$ or JP-61131486-$ or JP-60115266-$ or JP-06053463-$ or JP-05090610-$ or JP-63202062-$ or JP-62123773-$ or JP-62020376-$ or JP-61240675-$ or JP-61193484-$ or JP-61184883-$ or JP-60232788-$ or JP-60147128-$ or JP-58158973-$ or JP-58114459-$ or JP-57039583-$ or JP-56090564-$ or JP-56076559-$ or JP-55118678-$ or JP-53059381-$).did. | US-PGPUB; USPAT; JPO | OR | ON | 2004/12/09 12:58 |
| S20 | 23 | S19 and ((floating adj gate) near3 (mos of mosfet or transistor)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 12:58 |
| S21 | 20 | S19 and ((floating adj gate) near3 (mos of mosfet or transistor)).ti, ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 12:59 |

| S22 | 12 | S19 and ((floating adj gate) near3 (mos of mosfet or transistor)).ti, ab,clm. and ((first or second or third) near3 (transistor or mosfet or mos)).ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 12:59 |
|---|---|---|---|---|---|---|
| S23 | 13 | S19 and ((floating adj gate) near3 (mos of mosfet or transistor)).ti, ab,clm. and ((first or second or third) near5 (transistor or mosfet or mos)).ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 13:00 |
| S24 | 14 | S19 and ((floating adj gate) near5 (mos of mosfet or transistor)).ti, ab,clm. and ((first or second or third) near5 (transistor or mosfet or mos)).ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 13:00 |
| S25 | 11 | S19 and ((floating adj gate) near5 (mos of mosfet or transistor)).ti, ab,clm. with ((first or second or third) near5 (transistor or mosfet or mos)).ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 13:01 |
| S26 | 9 | S19 and ((floating adj gate) near5 (mos of mosfet or transistor)).ti, ab,clm. with ((first or second or third) near5 (transistor or mosfet or mos) with (dope or doped or doping or impurity or region or conductivity)).ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 13:03 |
| S27 | 0 | S19 and ((floating adj gate) near5 (mos of mosfet or transistor)).ti, ab,clm. with ((first or second or third) near5 (transistor or mosfet or mos) with ((n+ or p+ or heavy or heavily) near5 (dope or doped or doping or impurity or region or conductivity))).ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 13:05 |
| S28 | 13 | ((floating adj gate) near5 (mos of mosfet or transistor)).ti,ab,clm. with ((first or second or third) near5 (transistor or mosfet or mos) with ((n+ or p+ or heavy or heavily) near5 (dope or doped or doping or impurity or region or conductivity))).ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 13:05 |
| S29 | 14 | ((floating adj gate) near5 (mos of mosfet or transistor)).ti,ab,clm. with ((first or second or third) near5 (transistor or mosfet or mos) with ((ldd or hdd or n+ or p+ or heavy or heavily) near5 (dope or doped or doping or impurity or region or conductivity))).ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 13:07 |

| S30 | 0 | ((floating adj gate) near5 (mos of mosfet or transistor)).ti,ab,clm. with ((first or second or third) near5 (transistor or mosfet or mos) with ((ldd or hdd or n+ or p+ or heavy or heavily) near5 (dope or doped or doping or impurity or region or conductivity))) and (esd or electrostatic) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 13:10 |

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
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| S32 | 1 | ((floating adj gate) near5 (mos of mosfet or transistor)).ti,ab,clm. with ((first or second or third) near5 (transistor or mosfet or mos) with (((((ldd or hdd or n+ or p+ or heavy or heavily) near5 (dope or doped or doping or impurity or region or conductivity)))) or (n+ or p+ or hdd or ldd)) and (esd or electrostatic) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 13:12 |
| S33 | 145 | (floating adj gate).ti,ab,clm. and (esd or electrostatic).ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 13:13 |
| S34 | 44 | ((transistor or mosfet or mos) near5 (floating adj gate)).ti,ab, clm. and (esd or electrostatic).ti, ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 13:13 |

| S35 | 86 | (US-20040041215-$ or US-20040004231-$ or US-20020195648-$ or US-20020005544-$ or US-20010039091-$ or US-20020140023-$ or US-20020014656-$).did. or (US-6809386-$ or US-5589699-$ or US-5519240-$ or US-4495427-$ or US-6826128-$ or US-6008508-$ or US-6670679-$ or US-6610262-$ or US-6560080-$ or US-6448593-$ or US-6388922-$ or US-6373095-$ or US-6265251-$ or US-6239465-$ or US-6055143-$ or US-5986308-$ or US-5932916-$ or US-5909347-$ or US-5869873-$ or US-5844300-$ or US-5838033-$ or US-5272586-$ or US-5195010-$ or US-4087795-$ or US-3590343-$ or US-6825525-$).did. or (US-6680505-$ or US-6597048-$ or US-6556025-$ or US-6426529-$ or US-6175394-$ or US-6133601-$ or US-5986939-$ or US-5506159-$ or US-6034552-$ or US-6829200-$ or US-6014305-$ or US-5661686-$ or US-5243490-$).did. or (EP-497471-$).did. or (JP-05343696-$ or JP-04324980-$ or JP-61230376-$ or JP-61131486-$ or JP-60115266-$ or JP-06053463-$ or JP-05090610-$ or JP-63202062-$ or JP-62123773-$ or JP-62020376-$ or JP-61240675-$ or JP-61193484-$ or JP-61184883-$ or JP-60232788-$ or JP-60147128-$ or JP-58158973-$ or JP-58114459-$ or JP-57039583-$ or JP-56090564-$ or JP-56076559-$ or JP-55118678-$ or JP-53059381-$ or JP-2003007833-$ or JP-07254299-$ or JP-03174679-$ or JP-02035639-$).did. or (JP-62023685-$).did. or (WO-2004090195-$ or US-6556025-$ or KR-2003001809-$ or US-20020195648-$ or TW-507356-$ or US-6448593-$ or JP-11297861-$ or FR-2772989-$ or US-5844300-$ or US-5519240-$ or EP-497471-$ or DE-3121494-$).did. | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2004/12/09 13:15 |

| S36 | 27 | S35 and (p+ or n+ or ldd or hdd or ((heavily or heavy) near2 (dope or doped or doping)) or impurity or conductivity).ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 13:18 |
|-----|-----|-----|-----|-----|-----|-----|
| S37 | 27 | S35 and (p+ or n+ or ldd or hdd or ((heavily or heavy) near2 (dope or doped or doping)) or impurity or conductivity).ti,ab,clm. and (floating adj gate).ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 13:18 |
| S38 | 5144 | (p+ or n+ or ldd or hdd or ((heavily or heavy) near2 (dope or doped or doping)) or impurity or conductivity).ti,ab,clm. and (floating adj gate).ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 13:18 |
| S39 | 27 | S35 and (p+ or n+ or ldd or hdd or ((heavily or heavy) near2 (dope or doped or doping)) or impurity or conductivity).ti,ab,clm. and (floating adj gate).ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 13:20 |
| S40 | 13 | S35 and (p+ or n+ or ldd or hdd or ((heavily or heavy) near2 (dope or doped or doping)) or impurity or conductivity).ti,ab,clm. and ((transistor or mosfet or mos) near5 (floating adj gate)).ti,ab, clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 13:22 |
| S41 | 12 | S35 and (p+ or n+ or ldd or hdd or ((heavily or heavy) near2 (dope or doped or doping)) or impurity or conductivity).clm. and ((transistor or mosfet or mos) near5 (floating adj gate)).ti,ab, clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 13:22 |
| S42 | 11 | S35 and (p+ or n+ or ldd or hdd or ((heavily or heavy) near2 (dope or doped or doping)) or impurity or conductivity).clm. and ((transistor or mosfet or mos) near5 (floating adj gate)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/09 13:24 |

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| L6 | 16 | (floating near2 gate near2 transistor).clm. and (esd or electrostatic).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/10 11:28 |